Date: 6/28/2006 Time: 06:35:07



Inventor Name Search Result

Your Search was:

Last Name = MITAMURA First Name = NOBUAKI

Application#	Patent#	Status	Date Filed	Title	Inventor Name	
07557574	5030017	150	07/24/1990	ROLLING BEARING	MITAMURA, NOBUAKI	
07560445	5084116	150	07/31/1990	ROLLING CONTACT ELEMENT STEEL AND ROLLING BEARING MADE THEREOF	MITAMURA, NOBUAKI	
07572480	5085733	150	08/23/1990	ROLLING CONTACT PARTS STEEL AND ROLLING BEARING MADE THEREOF	MITAMURA, NOBUAKI	
07915503	Not Issued	161	07/20/1992	BALL AND ROLLER BEARING	MITAMURA, NOBUAKI	
07946638	5338377	150	09/18/1992	BALL-AND\ROLLER BEARING	MITAMURA, NOBUAKI	
08134588	5427457	150	10/12/1993	ROLLING BEARING	MITAMURA, NOBUAKI	
08242668	5413643	150	05/13/1994	ROLLING BEARING	MITAMURA, NOBUAKI	
08374179	Not Issued	166	01/18/1995	TOROIDAL-TYPE CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI	
08512419	5660647	150	08/08/1995	ROLLING BEARING WITH IMPROVED WEAR RESISTANCE	MITAMURA, NOBUAKI	
08519643	5626974	150	08/25/1995	ROLLING BEARING FOR USE UNDER HIGH TEMPERATURE CONDITIONS	, ,	
08536773	5672014	150	09/29/1995	ROLLING BEARINGS	MITAMURA, NOBUAKI	
08542828	5853660	150		\ \ \	MITAMURA, NOBUAKI	
08683195	<u>5958155</u>	150	07/18/1996	PROCESS FOR PRODUCING	MITAMURA,	

				THIN FILM	NOBUAKI
08745635	5855531	150	11/08/1996	COMPONENT PARTS OF A TOROIDAL-TYPE CONTINUOUSLY VARIABLE TRANSMISSION HAVING IMPROVED LIFE	MITAMURA, NOBUAKI
08763883	5887015	150	12/11/1996	HEATER MECHANISM FOR CRYSTAL PULLING APPARATUS\	MITAMURA, NOBUAKI
08877950	5989694	150	06/17/1997	ROLLING BEARING	MITAMURA, NOBUAKI
08955294	Not Issued	164	10/21/1997	ROLLING BEARING MADE OF IMPROVED BEARING STEEL	MITAMURA, NOBUAKI
09098980	6171414	150	06/17/1998	ROLLING BEARING	MITAMURA, NOBUAKI
09108174	6174257	150	07/01/1998	TOROIDAL/TYPE CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI
09181911	6174258	150	10/29/1998	TOROIDAL-TYPE CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI
09183630	6066068	150	10/30/1998	TOROIDAL TYPE CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI
09187607	6165100	150		HIGH-CLEANNESS STEEL AND TOROIDAL TYPE CONTINUOUSLY VARIABLE TRANSMISSION INCLUDING COMPONENTS SUCH AS INPUT/OUTPUT/DISCS, POWER ROLLER AND CAM DISC USING THE HIGH- CLEANNESS STEEL	MITAMURA, NOBUAKI
09226032	6174085	150		LINEAR GUIDE BEARING DEVICE	MITAMURA, NOBUAKI
09235052	6196946	150	01/21/1999	POWER ROLLER BEARING OF TOROIDAL\TYPE CONTINUOUSLY VARIABLE TRANSMISSION AND METHOD OF MANUFACTURING POWER ROLLER BEARING OF TOROIDAL TYPE CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI

09245931	Not Issued	161	02/08/1999	TEMPERATURE- INDEPENDENT OPTICAL ELEMENT	MITAMURA, NOBUAKI
09272731	6210542	150	11/04/1998	PROCESS FOR PRODUCING THIN FILM, THIN FILM AND OPTICAL INSTRUMENT INCLUDING THE SAME	MITAMURA, NOBUAKI
09339238	6332714	150	11	INDUCTION HARDENED ROLLING BEARING DEVICE	MITAMURA, NOBUAKI
09344380	6328669	150	06/25/1999	TOROIDAL TYPE CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI
09349204	6176806	150	07/07/1999	CAM DISK FOR TOROIDAL TYPE CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI
09358554	6478894	150	07/22/1999	ROLLING BRARING	MITAMURA, NOBUAKI
09379748	6152605	150	08/24/1999	BALL BEARING	MITAMURA, NOBUAKI
09401917	6358440	150	09/23/1999	PROCESS FOR PRODUCING THIN FILM, THIN FILM AND OPTICAL INSTRUMENT INCLUDING THE SAME	MITAMURA, NOBUAKI
09697179	6829053	150	10/27/2000	AIRGAP TYPE ETALON AND APPARATUS UTILIZING THE SAME	MITAMURA, NOBUAKI
09886122	6413188			TOROIDAL TYPE CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI
09939566	6646805	150	08/28/2001	APPARATUS FOR VARIABLE WAVELENGTH DISPERSION AND WAVELENGTH DISPERSION SLOPE	MITAMURA, NOBUAKI
09957413	6426022	150	09/20/2001	PROCESS FOR PRODUCING THIN FILM, THIN FILM AND OPTICAL INSTRUMENT INCLUDING THE SAME	MITAMURA, NOBUAKI
09984396	6807335	150	10/30/2001	WAVELENGTH CHARACTERISTIC VARIABLE APPARATUS	MITAMURA, NOBUAKI
10061307	6826318	150	02/04/2002	VARIABLE POLARIZATION PLANE ROTATOR AND OPTICAL DEVICE USING SAME	MITAMURA, NOBUAKI
10164438	6900940	150	06/10/2002	OPTICAL APRARATUS AND	MITAMURA,

1,	11 1	11	11	n \	H
			<u> </u>		NOBUAKI
10278868	Not Issued	41	10/24/2002	Device using a virtually-imaged phased array (VIPA) with an improved transmission wave characteristic of output light	MITAMURA, NOBUAKI
10286779	6862126	150	11/04/2002	TRANSMISSION WAVELENGTH CHARACTERISTICS VARIABLE OPTICAL ELEMENT, AND WAVELENGTH CHARACTERISTICS VARIABLE APPARATUS, OPTICAL AMPLIFIER, OPTICAL TRANSMISSION SYSTEM, AND CONTROL METHOD OF TRANSMISSION WAVELENGTH CHARACTERISTICS, USING SAME	MITAMURA, NOBUAKI
10310900	Not Issued	93	12/06/2002	ROLLING BEARING	MITAMURA, NOBUAKI
10340842	6909537	150	01/13/2003	DISPERSION COMPENSATOR WHOSE TRANSMISSION BAND IS FLATTENED	MITAMURA, NOBUAKI
10341380	6807008	150	01/14/2003	WAVELENGTH DISPERSION GENERATION APPARATUS, MULTI-FACED MIRROR USED FOR WAVELENGTH DISPERSION GENERATION APPARATUS, AND METHOD FOR MANUFACTURING THEREOF	MITAMURA, NOBUAKI
10351376	7016096	150	01/27/2003	TRANSMISSION WAVELENGTH CHARACTERISTICS VARIABLE OPTICAL ELEMENT, AND WAVELENGTH CHARACTERISTICS VARIABLE APPARATUS, OPTICAL AMPLIFIER, AND OPTICAL TRANSMISSION SYSTEM, USING SAME	MITAMURA, NOBUAKI
10410342	7037386	150	04/10/2003	ROLLING BEARING FOR CONTINUOUSLY VARIABLE TRANSMISSION	MITAMURA, NOBUAKI

10414308	6923576	150		MITAMURA, NOBUAKI
10500580	Not Issued	41	\ \	MITAMURA, NOBUAKI
(10510695)	Not Issued	41		MITAMURA, NOBUAKI
10512470	Not Issued	20	Silicon single crystal wafer and epitaxial wafer, and method for producing silicon single crystal	MITAMURA, NOBUAKI

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Carach Assathan Insurant	Last Name	First Name	
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Inventor Name Search Result

Your Search was:

Last Name = OHTA

First Name = TOMOHIKO

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Application#					Inventor Name
08655810	<u>5817171</u>	150	05/31/1996	APPARATUS AND METHOD FOR PRODUCING SINGLE CRYSTAL USING CZOCHRALSKI TECHNIQUE	OHTA, TOMOHIKO
08666654	5704973	150		AN APPARATUS AND METHOD FOR THE UNIFORM DISTRIBUTION OF CRYSTAL DEFECTS UPON A SILICON SINGLE CRYSTAL	ОНТА, ТОМОНІКО
08699719	5725661	250	07/01/1996	EQUIPMENT FOR PRODUCING SILICON SINGLE CRYSTALS	ОНТА, ТОМОНІКО
08760959	5766346	150	12/05/1996	APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL	ОНТА, ТОМОНІКО
08770499	5851283	150		METHOD AND APPARATUS FOR PRODUCTION OF SINGLE CRYSTAL	ОНТА, ТОМОНІКО
<u>08776776</u>	5972106	150	02/10/1997	DEVICE AND METHOD FOR PRODUCING SINGLE CRYSTAL	ОНТА, ТОМОНІКО
08786340	5882398	250		METHOD OF \\ MANUFACTURING SINGLE CRYSTAL OF SIDICON	ОНТА, ТОМОНІКО
08798472	5948163	250		APPARATUS FOR MANUFACTURING CRYSTALS ACCORDING TO THE CZOCHRALSKI METHOD, AND CRYSTALS MANUFACTURED BY THE MANUFACTURING METHOD	OHTA, TOMOHIKO
09090400	5938842	150		METHOD FOR PRODUCING A SINGLE CRYSTAL USING	ОНТА, ТОМОНІКО

			1	CZOCHRALSKI TECHNIQUE	
09125339	6071337	150	08/13/1998	APPARATUS AND METHOD FOR PRODUCING CRYSTALS BY THE CZOCHRALSKI METHOD AND CRYSTALS PRODUCED BY THIS METHOD	OHTA, TOMOHIKO
09270277	6153009	150	03/16/1999	METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL AND THE SILICON SINGLE CRYSTAL PRODUCED THEREBY	OHTA, TOMOHIKO
09270453	6156119	150	03/17/1999	SILICON SINGLE CRYSTAL AND METHOD FOR PRODUCING THE SAME	ОНТА, ТОМОНІКО
09290261	6117231	150	04/13/1999	METHOD OF MANUFACTURING SEMICONDUCTOR SILICON SINGLE CRYSTAL WAFER	ОНТА, ТОМОНІКО
09328278	6190452	150	06/08/1999	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING IT	ОНТА, ТОМОНІКО
09541462	7078203	150	03/31/2000	ISOLATED DNA ENCODING CULLIN REGULATORS ROC1 AND ROC2, ISOLATED PROTEIND ENCODED BY THE SAME, AND METHODS UTILIZING THE SAME	OHTA, TOMOHIKO
09646713	6565822	150	09/21/2000	EPITAXIAL SILICON WAFER, METHOD FOR PRODUCING THE SAME AND SUBTRATE FOR EPITAXIAL SILICON WAFER	ОНТА, ТОМОНІКО
09673480	Not Issued	161		Method for producing silicon single crystals	ОНТА, ТОМОНІКО
09674858	6423285	150	11/07/2000	Method for producing silicon single crystal and production apparatus therefor as well as crystal and silicon wafer produced by the method	ОНТА, ТОМОНІКО
09727275	6482260	150	11/30/2000	SILICON SINGLE CRYSTAL WAFER AND A METHOD FOR PRODUCING IT	ОНТА, ТОМОНІКО
09937132	6632280	150	09/21/2001	SINGLE ORYSTAL GROWING DEVICE	ОНТА, ТОМОНІКО
09959381	6592662	150	10/24/2001	METHOD FOR PREPARING	ОНТА, ТОМОНІКО

				SILICON SINGLE CRYSTAL AND SILICON SINGLE CRYSTAL	
09959593	6605152	150	10/31/2001	CATCH PAN FOR MELT LEAKAGE IN APPARATUS FOR PULLING SINGLE CRYSTAL	ОНТА, ТОМОНІКО
09979519	6632411	150	11/23/2001	SILICON WAFER AND METHOD FOR PRODUCING SILICON SINGLE CRYSTAL	ОНТА, ТОМОНІКО
10204278	6764548	150	08/20/2002	APPARATUS AND METHOD FOR PRODUCING SILICON SEMICONDUCTOR SINGLE CRYSTAL	ОНТА, ТОМОНІКО
10204935	6913646	150	08/27/2002	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING SILICON SINGLE CRYSTAL	ОНТА, ТОМОНІКО
10312921	6893499	150	12/26/2002	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR MANUFACTURING THE SAME	ОНТА, ТОМОНІКО
10500580	Not Issued	41	07/01/2004	AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER	ОНТА, ТОМОНІКО
10503721	Not Issued	41	08/06/2004	HEATER FOR MANUFACTURING A CRYSTAL	ОНТА, ТОМОНІКО
10510695	Not Issued	41) In		METHOD OF MANUFACTURING SILICON SINGLE CRYSTAL, SILICON SINGLE CRYSTAL AND SILICON WAFER	OHTA, TOMOHIKO
10512470	Not Issued	20	10/26/2004	Silicon single crystal wafer and epitaxial wafer, and method for producing silicon single crystal	ОНТА, ТОМОНІКО
10561865	Not Issued	30		Method for producing single crystal and single crystal	ОНТА, ТОМОНІКО
60127261	Not Issued	159		ISOLATION OF ROC1 AND ROC2	ОНТА, ТОМОНІКО
60166927	Not Issued	159	11/22/1999	ISOLATED DNA ENCODING CULLIN REGULATORS ROCI AND ROC2, ISOLATED PROTEINS ENCODED BY SAME, AND METHODS UTILIZING THE SAME	ОНТА, ТОМОНІКО

605412	287	Not Issued	159	Tumor suppressor BARD1 ubiquitina nucleophosmin and CDK2	ates	ОНТА, ТОМОНІКО
607274	429	Not Issued	20	Method for the ubicommon subunits of polymerases	•	ОНТА, ТОМОНІКО
60750	877	Not Issued	20	Functional interact BRCA1 and HERO protein deficient in x: BRCA1 degrada HERC2	C2, a large n rjs/jdf2 mice	OHTA, TOMOHIKO
102619	956	6862014	150	DISPLAY DRIVII APPARATUS AN CONTROL MET	ID DRIVING	OHTANI, TOMOHIKO
104152	283	Not Issued	30	Display device and thereof		OHTANI, TOMOHIKO

Inventor Search Completed: No Records to Display.

	Last Name	First Name	
Search Another: Inventor	Ohta	Tomohiko	-Seardh

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Date: 6/28/2006 Time: 06:35:38



Inventor Name Search Result

Your Search was:

Last Name = FUSEGAWA

First Name = IZUMI

Application#	Patent#	Status	Date Filed	Title	Inventor Name
06941624	Not Issued	161	12/11/1986	METHOD AND APPARATUS FOR CZOCHRALSKI SINGLE CRYSTAL GROWING	FUSEGAWA, IZUMI
07242414	4956153	250	09/09/1988	APPARATUS FOR CZOCHRALSKI SINGLE CRYSTAL GROWING	FUSEGAWA, IZUMI
07496750	5110404	150	03/21/1990	METHOD FOR HEAT PROCESSING OF SILICON	FUSEGAWA, IZUMI
07703750	Not Issued	166	05/21/1991	METHOD FOR PULLING UP SEMICONDUCTOR SINGLE CRYSTAL	FUSEGAWA, IZUMI
07713848	5306387	150	06/12/1991	METHOD FOR PULLING UP SEMICONDUCTOR SINGLE CRYSTAL	FUSEGAWA, IZUMI
07729026	Not Issued	161	07/12/1991	METHOD FOR PULLING SEMICONDUCTOR SINGLE CRYSTAL	FUSEGAWA, IZUMI
07796385	5688319	150	11/22/1991	METHOD FOR TESTING ELECTRICAL PROPERTIES OF SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI
07850506	5262338	250	03/13/1992	METHOD FOR FABRICATION OF SEMICONDUCTOR DEVICE	FUSEGAWA, IZUMI
07850915	Not Issued	166	03/13/1992	HEAT TREATMENT OF SI SINGLE CRYSTAL	FUSEGAWA, IZUMI
07850916	<u>5386796</u>	150		METHOD FOR TESTING QUALITY OF SILICON WAFER	FUSEGAWA, IZUMI
07852612	<u>5248378</u>	150		METHOD AND APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI
07953918	5359959	150	09/30/1992	METHOD FOR PULLING UP	FUSEGAWA, IZUMI

				SEMI-CONDUCTOR SINGLE CRYSTAL	
07961182	5462010	250	10/14/1992	APPARATUS FOR SUPPLYING GRANULAR RAW MATERIAL FOR A SEMICONDUCTOR SINGLE CRYSTAL PULLING APPARATUS	FUSEGAWA, IZUMI
07961764	5373805	250	10/15/1992	SINGLE CRYSTAL PULLING APPARATUS	FUSEGAWA, IZUMI
08011744	5340434	250	02/01/1993	PROCESS FOR PRODUCING SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI
08012172	5361721	250	02/02/1993	SINGLE CRYSTAL PULLING APPARATUS	FUSEGAWA, IZUMI
08108285	Not Issued	166	08/19/1993	HEAT TREATMENT OF SI SINGLE CRYSTAL	FUSEGAWA, IZUMI
<u>0819Ó604</u>	Not Issued	166	02/02/1994	CRUCIBLE FOR PULLING SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI
08238722	5534112	150	05/05/1994	METHOD FOR TESTING ELECTRICAL PROPERTIES OF SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI
08293214	Not Issued	166	08/19/1994	APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL GROWN BY CZOCHRALSKI METHOD	FUSEGAWA, IZUMI
08395837	5501172	150	02/28/1995	METHOD OF GROWING SILICON SINGLE CRYSTALS	FUSEGAWA, IZUMI
08445029	Not Issued	166	II I	HEAT TREATMENT OF SI SINGLE CRYSTAL	FUSEGAWA, IZUMI
08510436	5720809	250	11	CRUCIBLE FOR PULLING SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI
08552164	Not Issued	166	11/02/1995	APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL GROWN BY CZOCHRALSKI METHOD	FUSEGAWA, IZUMI
08699719	5725661	250	II I	EQUIPMENT FOR PRODUCING SILICON SINGLE CRYSTALS	FUSEGAWA, IZUMI
08754784	5938841	150	11 9	DEVICE FOR PRODUCING SINGLE CRYSTAL	FUSEGAWA, IZUMI
08760959	5766346			APPARATUS FOR PRODUCING SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI
08770499	5851283	150	12/20/1996	METHOD AND APPARATUS	FUSEGAWA, IZUMI

■.							
				FOR PRODUCTION OF SINGLE CRYSTAL			
08773351	5871583	150	12/26/1996	AN APPARATUS FOR PRODUCING SILICON CRYSTAL	FUSEGAWA, IZUMI		
08916291	5834322	250	08/22/1997	HEAT TREATMENT OF SI SINGLE CRYSTAL	FUSEGAWA, IZUMI		
09270277	6153009	150	03/16/1999	METHOD FOR PRODUCING A SILICON SINGLE CRYSTAL AND THE SILICON SINGLE CRYSTAL PRODUCED THEREBY	FUSEGAWA, IZUMI		
09290261	6117231	150	04/13/1999	METHOD OF MANUFACTURING SEMICONDUCTOR SILICON SINGLE CRYSTAL WAFER	FUSEGAWA, IZUMI		
09429343	6387466	150	10/28/1999	SINGLE-CRYSTAL SILICON WAFER	FUSEGAWA, IZUMI		
09646713	6565822	150	09/21/2000	EPITAXIAL SILICON WAFER, METHOD FOR PRODUCING THE SAME AND SUBTRATE FOR EPITAXIAL SILICON WAFER	FUSEGAWA, IZUMI		
09673480	Not Issued	161		Method for producing silicon single crystals	FUSEGAWA, IZUMI		
09674858	6423285	150		Method for producing silicon single crystal and production apparatus therefor as well as crystal and silicon wafer produced by the method	FUSEGAWA, IZUMI		
09937132	6632280	150		SINGLE CRYSTAL GROWING DEVICE	FUSEGAWA, IZUMI		
09959381	6592662	150	10/24/2001	METHOD FOR PREPARING SILICON SINGLE CRYSTAL AND SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI		
09979519	6632411	150	11/23/2001	SILICON WAFER AND METHOD FOR PRODUCING SILICON SINGLE CRYSTAL	FUSEGAWA, IZUMI		
10204278	6764548	150		APPARATUS AND METHOD FOR PRODUCING SILICON SEMICONDUCTOR SINGLE CRYSTAL	FUSEGAWA, IZUMI		
10204935	<u>6913646</u>	150		SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING SILICON	FUSEGAWA, IZUMI		

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10312921	6893499	150	12/26/2002	SINGLE CRYSTAL SILICON SINGLE CRYSTAL WAFER AND METHOD FOR MANUFACTURING THE SAME	FUSEGAWA, IZUMI		
10500580	Not Issued	41	07/01/2004	AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER	FUSEGAWA, IZUMI		
10510695	Not Issued	41	10/08/2004	METHOD OF MANUFACTURING SILICON SINGLE CRYSTAL, SILICON SINGLE CRYSTAL AND SILICON WAFER	FUSEGAWA, IZUMI		
10512470	Not Issued	20	10/26/2004	Silicon single crystal wafer and epitaxial wafer, and method for producing silicon single crystal	FUSEGAWA, IZUMI		
10516347	Not Issued	20	11/30/2004	Graphite heater for producing single crystal, single crystal productin system and single crystal productin method	FUSEGAWA, IZUMI		
10538878	Not Issued	41	06/14/2005	Method of producing p-doped silicon single crystal and p-doped n-type silicon single crystal wafer	FUSEGAWA, IZUMI		
10542376	Not Issued	30	II I	AN SOI WAFER AND A METHOD FOR PRODUCING THE SAME	FUSEGAWA, IZUMI		
<u>10561865</u>	Not Issued	30		Method for producing single crystal and single crystal	FUSEGAWA, IZUMI		
10568186	Not Issued	19	01/01/0001	Method for producing a single crystal and silicon single crystal wafer	FUSEGAWA, IZUMI		

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Inventor Name Search Result

Your Search was:

Last Name = SAKURADA First Name = MASAHIRO

Application#	Patent#	Status	Date Filed	Title	Inventor Name		
08498894	5609682	150	07/06/1995	A METHOD FOR THE PREPARATION OF SILICON SINGLE CRYSTAL	SAKURADA, MASAHIRO		
08565100	5667584	150	11/30/1995	METHOD FOR THE PREPARATION OF A SINGLE CRYSTAL OF SILICON WITH DECREASED CRYSTAL DEFECTS	SAKURADA, MASAHIRO		
08655810	5817171	150	05/31/1996	APPARATUS AND METHOD FOR PRODUCING SINGLE CRYSTAL USING CZOCHRALSKI TECHNIQUE	SAKURADA, MASAHIRO		
08660198	5728211	250	06/03/1996	SILICON SINGLE CRYSTAL WITH LOW DEFECT DENSITY AND METHOD OF PRODUCING SAME	SAKURADA, MASAHIRO		
08666654	5704973	150	06/18/1996	AN APPARATUS AND METHOD FOR THE UNIFORM DISTRIBUTION OF CRYSTAL DEFECTS UPON A SILICON SINGLE CRYSTAL	SAKURADA, MASAHIRO		
08768282	5730800	150	12/17/1996	FUSED SILICA GLASS CRUCIBLE	SAKURADA, MASAHIRO		
08798472	5948163	250		APPARATUS FOR MANUFACTURING CRYSTALS ACCORDING TO THE CZOCHRALSKI METHOD, AND CRYSTALS MANUFACTURED BY THE MANUFACTURING METHOD	SAKURADA, MASAHIRO		
09090400	5938842	150		METHOD FOR PRODUCING A SINGLE CRYSTAL USING CZOCHRALSKI TECHNIQUE	SAKURADA, MASAHIRO		

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09125339			08/13/1998	APPARATUS AND METHOD FOR PRODUCING CRYSTALS BY THE CZOCHRALSKI METHOD AND CRYSTALS PRODUCED BY THIS METHOD	SAKURADA, MASAHIRO	
09232561	6174364	150	01/15/1999	METHOD FOR PRODUCING SILICON MONOCRYSTAL AND SILICON MONOCRYSTAL WAFER	SAKURADA, MASAHIRO	
09328278	6190452	150	06/08/1999	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING IT	SAKURADA, MASAHIRO	
09646713	6565822	150	09/21/2000	EPITAXIAL SILICON WAFER, METHOD FOR PRODUCING THE SAME AND SUBTRATE FOR EPITAXIAL SILICON WAFER	SAKURADA, MASAHIRO	
09727275	6482260	150	11/30/2000	SILICON SINGLE CRYSTAL WAFER AND A METHOD FOR PRODUCING IT	SAKURADA, MASAHIRO	
10204935	6913646	150	08/27/2002	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR PRODUCING SILICON SINGLE CRYSTAL	SAKURADA, MASAHIRO	
10312921	6893499	150	12/26/2002	SILICON SINGLE CRYSTAL WAFER AND METHOD FOR MANUFACTURING THE SAME	SAKURADA, MASAHIRO	
10500580	Not Issued	41	07/01/2004	AN SOI WAFER AND A METHOD FOR PRODUCING AN SOI WAFER	SAKURADA, MASAHIRO	
<u>10512470</u>	Not Issued	20		Silicon single crystal wafer and epitaxial wafer, and method for producing silicon single crystal	SAKURADA, MASAHIRO	
10516347	Not Issued	20		Graphite heater for producing single crystal, single crystal productin system and single crystal productin method	SAKURADA, MASAHIRO	
10530557	Not Issued	20		Annealed wafer and anneald wafer manufacturing method	SAKURADA, MASAHIRO	
10538878	Not Issued	41	06/14/2005	Method of producing p-doped	SAKURADA, MASAHIRO	
10542376	Not	30	07/14/2005	AN SOI WAFER AND A	SAKURADA,	

	Issued			METHOD FOR PRODUCING THE SAME	MASAHIRO
10546693	Not Issued	20	08/22/2005	An soi wafer and a method for producing the same	SAKURADA, MASAHIRO
10560581	Not Issued	19		Method for producing a single crystal and a single crystal	SAKURADA, MASAHIRO
10561205	Not Issued	20	02/03/2006	Process for producing single crystal and single crystal	SAKURADA, MASAHIRO
10561865	Not Issued	30	02/20/2006		SAKURADA, MASAHIRO

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Tomohiko O Izumi Fuseo Masahiro S Atsushi Oza ** CONTINUING I This applica ** FOREIGN APP JAPAN 200	Ohta, gawa sakura aki, Finanti on interest of the part	ra, Fukushima, JAPAN Gunma, JAPAN; , Fukushima, JAPAN; ida, Fukushima, JAPA ukushima, JAPAN; a 371 of PCT/JP04/0 TIONS ************************************	N; * 07252 05						
Foreign Priority claime 35 USC 119 (a-d) cond met Verified and Acknowledged	STATE OR COUNTRY JAPAN	DRA	EETS TOTAL IN CLAIMS 9 20			INDEPENDENT CLAIMS 1			
Acknowledged Examiner's Signature Initials ADDRESS 25944 TITLE Method for producing single crystal and single crystal									
FILING FEE FEES: Authority has been given in Paper RECEIVED No to charge/credit DEPOSIT ACCOUNT No for following:							Fees 6 Fees (7 Fees (8 Fees (ner	Proce	essing Ext. of